DIXYS

Advance Technical Information

IXTQ470P2

PolarP2[™] Power MOSFET

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode



Symbol	Test Conditions	Maximum Ratings			
V _{dss}	$T_{J} = 25^{\circ}C$ to 150°C	500	V		
V _{dgr}	$T_{J} = 25^{\circ}C$ to 150°C, $R_{GS} = 1M\Omega$	500	V		
V _{GSS}	Continuous	± 30	V		
V _{GSM}	Transient	± 40	V		
I _{D25}	$T_{c} = 25^{\circ}C$	42	A		
I _{DM}	$T_{c} = 25^{\circ}C$, Pulse Width Limited by T_{JM}	126	A		
I _A	$T_c = 25^{\circ}C$	42	A		
E _{AS}	$T_c = 25^{\circ}C$	1.3	J		
dv/dt	$I_{_{S}} \leq I_{_{DM}}, V_{_{DD}} \leq V_{_{DSS}}, T_{_{J}} \leq 150^{\circ}C$	10	V/ns		
P _D	$T_c = 25^{\circ}C$	830	W		
T _J		-55 +150	⊃°		
T _{JM}		150	⊃°		
T _{stg}		-55 +150	⊃°		
T _L	Maximum Lead Temperature for Soldering	300	O°		
T _{SOLD}	Plastic Body for 10s	260	O°		
M _d	Mounting Torque	1.13/10	Nm/lb.in.		
Weight		5.5	g		

TO-3P		
	G D S	

Tab

G = Gate D = DrainS = Source Tab = Drain

Features

- Avalanche Rated
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

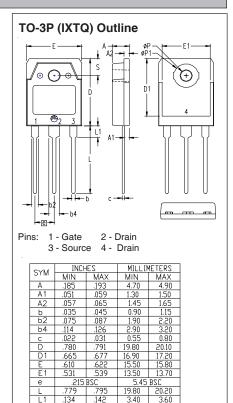
Symbol	Test Conditions	Chara	Characteristic Values			
$(T_{J} = 25^{\circ}C)$	C, Unless Otherwise Specified)	Min.	Тур.	Max		
BV _{DSS}	$V_{_{\rm GS}} = 0V, I_{_{\rm D}} = 250 \mu A$	500			V	
$V_{GS(th)}$	$V_{_{\mathrm{DS}}} = V_{_{\mathrm{GS}}}, I_{_{\mathrm{D}}} = 250 \mu \mathrm{A}$	2.5		4.5	V	
I _{gss}	$V_{gs} = \pm 30V, V_{ds} = 0V$			± 100	nA	
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$			5	μA	
	T _J = 125	С°		50	μA	
R _{DS(on)}	$V_{_{ m GS}}$ = 10V, $I_{_{ m D}}$ = 0.5 • $I_{_{ m D25}}$, Note 1			145	mΩ	

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$(T_{J} = 25)$	5°C Ui	nless Otherwise Specified)	Min.	Тур.	Max.	
g _{fs}		$V_{_{DS}} = 20V, I_{_{D}} = 0.5 \bullet I_{_{D25}}, Note 1$	23	36	S	
C _{iss})			5400	pF	
\mathbf{C}_{oss}	}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		545	pF	
\mathbf{C}_{rss}	J			44	pF	
t _{d(on)})	Resistive Switching Times		23	ns	
t _r		•		12	ns	
t _{d(off)}	($V_{GS} = 10V, V_{DS} = 0.5 \bullet V_{DSS}, I_{D} = 0.5 \bullet I_{D25}$ $R_{G} = 3\Omega \text{ (External)}$		42	ns	
t _r	J			9	ns	
Q _{g(on)})			88	nC	
Q _{gs}	}	$V_{\rm GS} = 10V, V_{\rm DS} = 0.5 \cdot V_{\rm DSS}, I_{\rm D} = 0.5 \cdot I_{\rm D25}$		30	nC	
Q_{gd}	J			31	nC	
R _{thJC}					0.15 °C/W	
$\mathbf{R}_{_{\mathrm{thCS}}}$				0.25	°C/W	



.142 .134

.280

6.90 4.90

40

Ø

ØP1 S

.126

.272. 193. All metal area are tin plated.

Source-Drain Diode

Symbol (T _J = 25°C U	Test Conditions nless Otherwise Specified)	Cha Min.	racteristic Typ.	Values Max.	
I _s	$V_{GS} = 0V$			42	Α
I _{SM}	Repetitive, Pulse Width Limited by $\mathrm{T_{_{JM}}}$			168	А
V _{sd}	$I_{F} = I_{S}, V_{GS} = 0V$, Note 1			1.5	V
t _{rr}	$I_F = 21A$, -di/dt = 100A/µs		400		ns
	$V_{_{\rm R}} = 100V, V_{_{ m GS}} = 0V$				

Note 1. Pulse test, $t \le 300 \mu s$, duty cycle, $d \le 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B	2 7,071,537	

Mouser Electronics

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